

Editorial

It is my great pleasure to announce the publication of a special JSTS issue on the 12th Korean Conference on Semiconductors (KCS 2005) held in Seoul, from Feb. 24-25, 2005. Among the 656 outstanding papers presented at the Conference, nine have been chosen by a committee of 12 technical experts to be published in the special issue of JSTS.

The first paper by M. G. Jang et al. describes scalability of Schottky barrier MOSFETs for nano-regime applications. The next paper written by S. Y. Kim et al. discusses enhanced hole injections in organic light emitting diode using a rhodium oxide - coated anode. The third paper is by W. J. Cho et al., and it addresses characterizations of interface-state density between top silicon and buried oxide on nano-SOI substrate by using Pseudo-MOSFETs. The fourth paper written by J. H. Um et al. shows ViP: a practical approach for a hardware/software co-design. The next paper written by S. W. Han et al. introduces a low dark current CMOS image sensor pixel with a photodiode structure enclosed by a P-well. The sixth paper written by K. Y. Park et al. reports the characteristics of Al₂O₃ /HfO₂ laminated AlGaIn/GaN MIS-HFET. The seventh paper by H. J. Na et al. discusses 4H-SiC planar MESFET for microwave power device applications. The eighth paper written by D. S. Kil et al. explains the theoretical calculation and experimental verification of the Hf/Al concentration ratio in nano-mixed Hf_xAl_{1-x}O₂ films prepared by atomic layer deposition. The ninth paper written by K. H. Lee et al. discusses the green and blue light emitting InN/GaN quantum wells with nanosize structures grown by a metalorganic chemical vapor deposition.

I would like to express my gratitude to all the authors for submitting excellent papers.

Sung-Wook Park
Guest editor of this special issue



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